

# **FDS7766S**

## **30V N-Channel PowerTrench<sup>®</sup> MOSFET**

### **General Description**

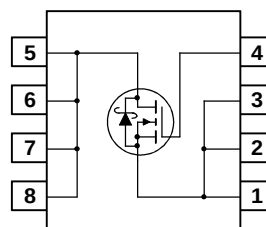
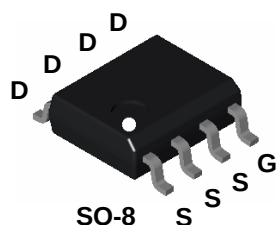
The FDS7766S is designed to replace a single SO-8 MOSFET and Schottky diode in synchronous DC:DC power supplies. This 30V MOSFET is designed to maximize power conversion efficiency, providing a low  $R_{DS(ON)}$  and low gate charge. The FDS7766S includes an integrated Schottky diode using Fairchild's monolithic SyncFET technology.

### **Applications**

- Synchronous rectifier
- DC/DC converter

### **Features**

- 17 A, 30 V  $R_{DS(ON)} = 5.5 \text{ m}\Omega @ V_{GS} = 10 \text{ V}$   
 $R_{DS(ON)} = 6.5 \text{ m}\Omega @ V_{GS} = 4.5 \text{ V}$
- High performance trench technology for extremely low  $R_{DS(ON)}$
- High power and current handling capability
- Fast switching



### **Absolute Maximum Ratings** $T_A = 25^\circ\text{C}$ unless otherwise noted

| Symbol         | Parameter                                        | Ratings         | Units            |
|----------------|--------------------------------------------------|-----------------|------------------|
| $V_{DSS}$      | Drain-Source Voltage                             | 30              | V                |
| $V_{GSS}$      | Gate-Source Voltage                              | $\pm 16$        | V                |
| $I_D$          | Drain Current – Continuous (Note 1a)             | 17              | A                |
|                | – Pulsed                                         | 60              |                  |
| $P_D$          | Power Dissipation for Single Operation (Note 1a) | 2.5             | W                |
|                | (Note 1b)                                        | 1.2             |                  |
|                | (Note 1c)                                        | 1.0             |                  |
| $T_J, T_{STG}$ | Operating and Storage Junction Temperature Range | $-55$ to $+150$ | $^\circ\text{C}$ |

### **Thermal Characteristics**

|                 |                                                   |     |                    |
|-----------------|---------------------------------------------------|-----|--------------------|
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient (Note 1a) | 50  | $^\circ\text{C/W}$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient (Note 1c) | 125 | $^\circ\text{C/W}$ |
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case (Note 1)     | 25  | $^\circ\text{C/W}$ |

### **Package Marking and Ordering Information**

| Device Marking | Device   | Reel Size | Tape width | Quantity   |
|----------------|----------|-----------|------------|------------|
| FDS7766S       | FDS7766S | 13"       | 12mm       | 2500 units |

**Electrical Characteristics** $T_A = 25^\circ\text{C}$  unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Units |
|--------|-----------|-----------------|-----|-----|-----|-------|
|--------|-----------|-----------------|-----|-----|-----|-------|

**Off Characteristics**

|                                      |                                           |                                                         |    |    |           |                      |
|--------------------------------------|-------------------------------------------|---------------------------------------------------------|----|----|-----------|----------------------|
| $BV_{DSS}$                           | Drain–Source Breakdown Voltage            | $V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$                | 30 |    |           | V                    |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | $I_D = 15\text{ mA}$ , Referenced to $25^\circ\text{C}$ |    | 23 |           | mV/ $^\circ\text{C}$ |
| $I_{DSS}$                            | Zero Gate Voltage Drain Current           | $V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}$             |    |    | 500       | $\mu\text{A}$        |
| $I_{GSS}$                            | Gate–Body Leakage                         | $V_{GS} = \pm 16\text{ V}, V_{DS} = 0\text{ V}$         |    |    | $\pm 100$ | nA                   |

**On Characteristics** (Note 2)

|                                        |                                                |                                                                                                                                                                 |    |                   |                   |                      |
|----------------------------------------|------------------------------------------------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------|----|-------------------|-------------------|----------------------|
| $V_{GS(th)}$                           | Gate Threshold Voltage                         | $V_{DS} = V_{GS}, I_D = 1\text{ mA}$                                                                                                                            | 1  | 1.3               | 3                 | V                    |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate Threshold Voltage Temperature Coefficient | $I_D = 15\text{ mA}$ , Referenced to $25^\circ\text{C}$                                                                                                         |    | –2                |                   | mV/ $^\circ\text{C}$ |
| $R_{DS(on)}$                           | Static Drain–Source On–Resistance              | $V_{GS} = 10\text{ V}, I_D = 17\text{ A}$<br>$V_{GS} = 4.5\text{ V}, I_D = 15.5\text{ A}$<br>$V_{GS} = 10\text{ V}, I_D = 17\text{ A}, T_J = 125^\circ\text{C}$ |    | 4.0<br>4.6<br>5.7 | 5.5<br>6.5<br>7.2 | m $\Omega$           |
| $I_{D(on)}$                            | On–State Drain Current                         | $V_{GS} = 10\text{ V}, V_{DS} = 5\text{ V}$                                                                                                                     | 30 |                   |                   | A                    |
| $g_{FS}$                               | Forward Transconductance                       | $V_{DS} = 10\text{ V}, I_D = 17\text{ A}$                                                                                                                       |    | 91                |                   | S                    |

**Dynamic Characteristics**

|           |                              |                                                                      |  |      |  |          |
|-----------|------------------------------|----------------------------------------------------------------------|--|------|--|----------|
| $C_{iss}$ | Input Capacitance            | $V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V},$<br>$f = 1.0\text{ MHz}$ |  | 4785 |  | pF       |
| $C_{oss}$ | Output Capacitance           |                                                                      |  | 825  |  | pF       |
| $C_{rss}$ | Reverse Transfer Capacitance |                                                                      |  | 290  |  | pF       |
| $R_G$     | Gate Resistance              | $V_{GS} = 15\text{ mV}, f = 1.0\text{ MHz}$                          |  | 1.3  |  | $\Omega$ |

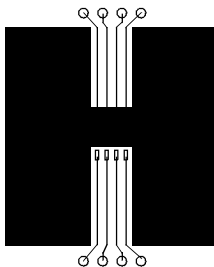
**Switching Characteristics** (Note 2)

|              |                     |                                                                                                |  |    |     |    |
|--------------|---------------------|------------------------------------------------------------------------------------------------|--|----|-----|----|
| $t_{d(on)}$  | Turn–On Delay Time  | $V_{DD} = 15\text{ V}, I_D = 1\text{ A},$<br>$V_{GS} = 10\text{ V}, R_{GEN} = 6\text{ }\Omega$ |  | 12 | 22  | ns |
| $t_r$        | Turn–On Rise Time   |                                                                                                |  | 12 | 22  | ns |
| $t_{d(off)}$ | Turn–Off Delay Time |                                                                                                |  | 82 | 132 | ns |
| $t_f$        | Turn–Off Fall Time  |                                                                                                |  | 30 | 49  | ns |
| $Q_g$        | Total Gate Charge   | $V_{DS} = 15\text{ V}, I_D = 17\text{ A},$<br>$V_{GS} = 5\text{ V}$                            |  | 41 | 58  | nC |
| $Q_{gs}$     | Gate–Source Charge  |                                                                                                |  | 11 |     | nC |
| $Q_{gd}$     | Gate–Drain Charge   |                                                                                                |  | 9  |     | nC |

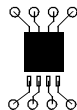
**Drain–Source Diode Characteristics and Maximum Ratings**

|                 |                                                       |                                                                               |  |     |     |    |
|-----------------|-------------------------------------------------------|-------------------------------------------------------------------------------|--|-----|-----|----|
| I <sub>S</sub>  | Maximum Continuous Drain–Source Diode Forward Current |                                                                               |  |     | 3.5 | A  |
| V <sub>SD</sub> | Drain–Source Diode Forward Voltage                    | V <sub>GS</sub> = 0 V, I <sub>S</sub> = 3.5 A (Note 2)                        |  | 0.4 | 0.7 | V  |
| t <sub>rr</sub> | Schottky Diode Reverse Recovery                       | I <sub>F</sub> = 17 A,<br>dI <sub>F</sub> /d <sub>t</sub> = 300 A/μs (Note 2) |  | 27  |     | ns |
| Q <sub>rr</sub> |                                                       |                                                                               |  | 28  |     | nC |

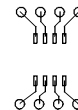
**Notes:** 1.  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a)  $50^\circ\text{C/W}$  when mounted on a  $1\text{ in}^2$  pad of 2 oz copper



b)  $105^\circ\text{C/W}$  when mounted on a  $.04\text{ in}^2$  pad of 2 oz copper



c)  $125^\circ\text{C/W}$  when mounted on a minimum pad.

Scale 1 : 1 on letter size page

2. Pulse Test: Pulse Width  $< 300\mu\text{s}$ , Duty Cycle  $< 2.0\%$

# Typical Characteristics

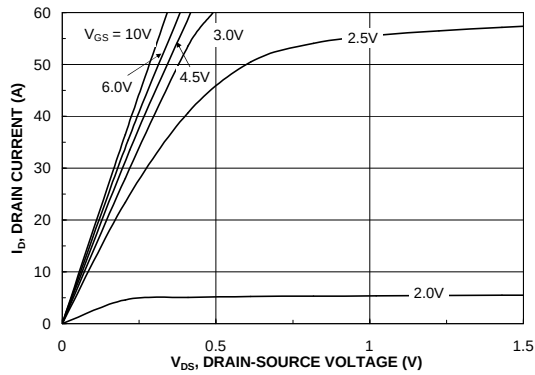


Figure 1. On-Region Characteristics.

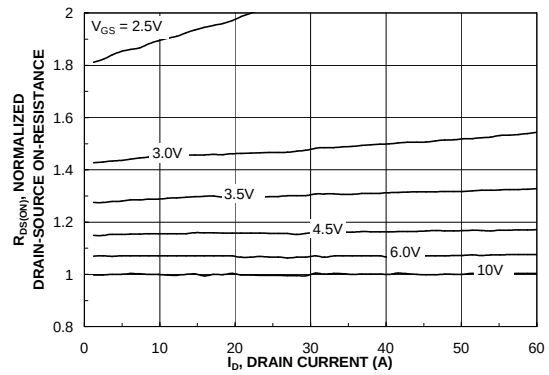


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

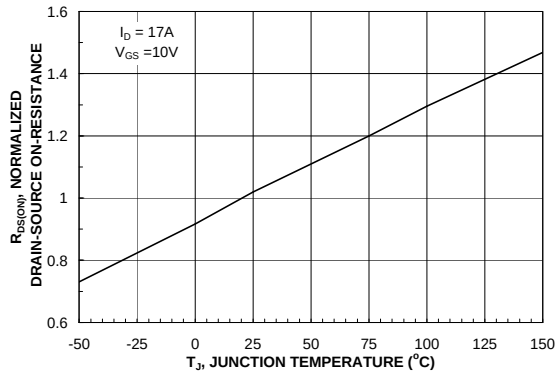


Figure 3. On-Resistance Variation with Temperature.

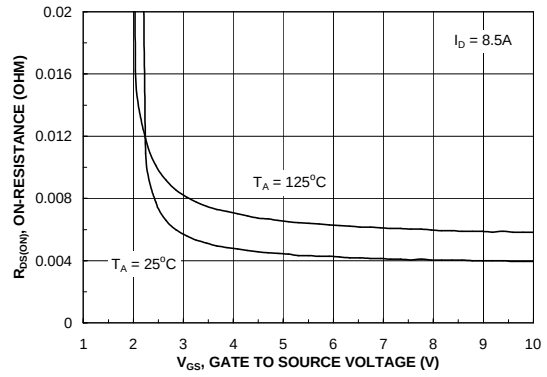


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

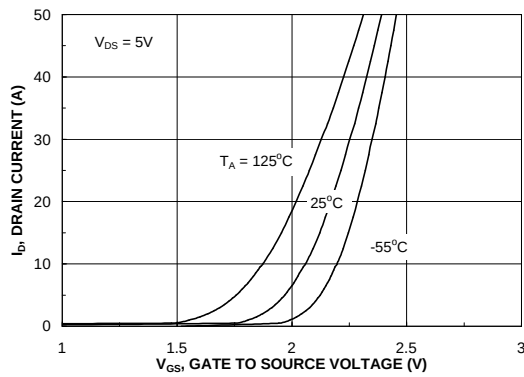


Figure 5. Transfer Characteristics.

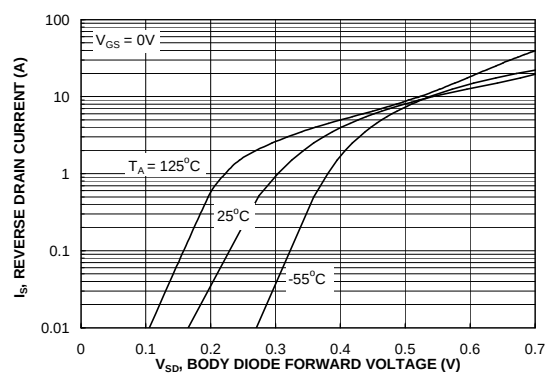


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

## Typical Characteristics

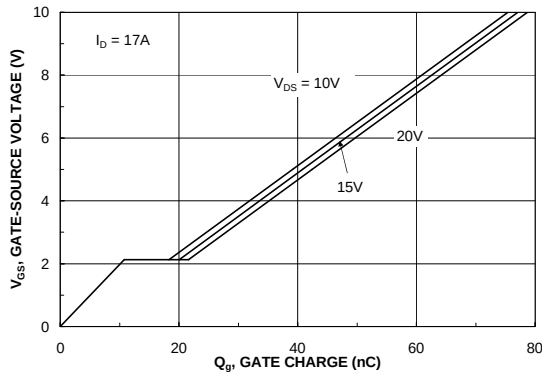


Figure 7. Gate Charge Characteristics.

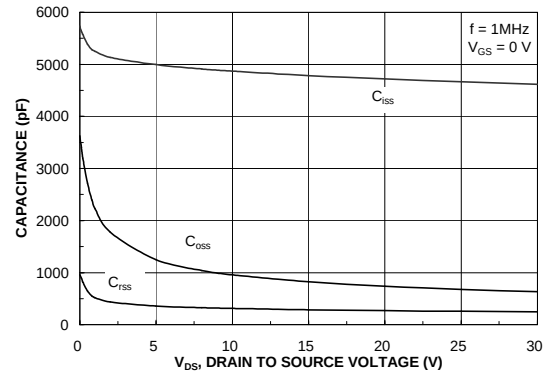


Figure 8. Capacitance Characteristics.

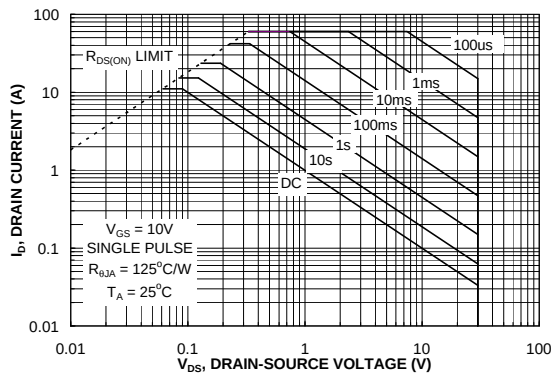


Figure 9. Maximum Safe Operating Area.

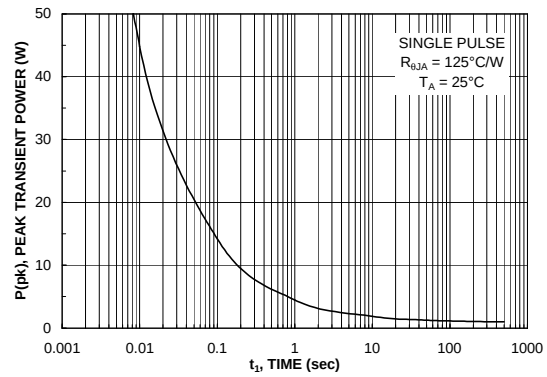


Figure 10. Single Pulse Maximum Power Dissipation.

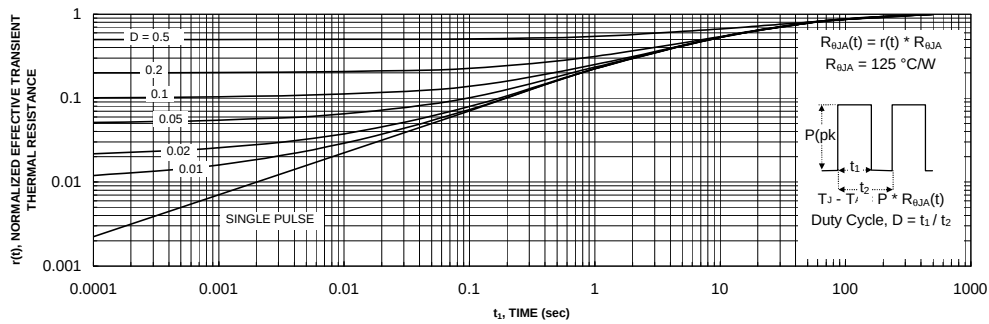


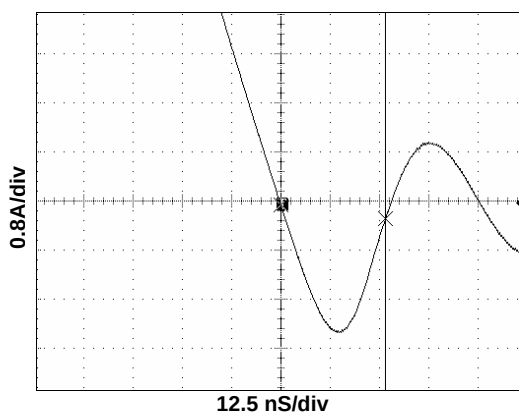
Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.

## Typical Characteristics (continued)

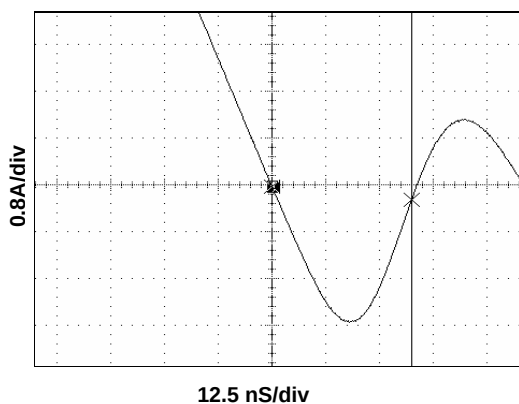
### SyncFET Schottky Body Diode Characteristics

Fairchild's SyncFET process embeds a Schottky diode in parallel with PowerTrench MOSFET. This diode exhibits similar characteristics to a discrete external Schottky diode in parallel with a MOSFET. Figure 12 shows the reverse recovery characteristic of the FDS7766S.



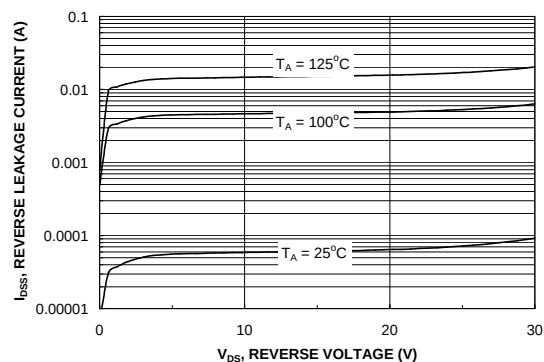
**Figure 12. FDS7766S SyncFET body diode reverse recovery characteristic.**

For comparison purposes, Figure 13 shows the reverse recovery characteristics of the body diode of an equivalent size MOSFET produced without SyncFET (FDS7766).



**Figure 13. Non-SyncFET (FDS7766) body diode reverse recovery characteristic.**

Schottky barrier diodes exhibit significant leakage at high temperature and high reverse voltage. This will increase the power in the device.



**Figure 14. SyncFET body diode reverse leakage versus drain-source voltage and temperature**

## TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

|                                      |                     |                    |                     |                 |
|--------------------------------------|---------------------|--------------------|---------------------|-----------------|
| ACEx™                                | FACT™               | ImpliedDisconnect™ | PACMAN™             | SPM™            |
| ActiveArray™                         | FACT Quiet Series™  | ISOPLANAR™         | POP™                | Stealth™        |
| Bottomless™                          | FAST®               | LittleFET™         | Power247™           | SuperSOT™-3     |
| CoolFET™                             | FASTr™              | MicroFET™          | PowerTrench®        | SuperSOT™-6     |
| CROSSVOLT™                           | FRFET™              | MicroPak™          | QFET®               | SuperSOT™-8     |
| DOME™                                | GlobalOptoisolator™ | MICROWIRE™         | QS™                 | SyncFET™        |
| EcoSPARK™                            | GTO™                | MSX™               | QT Optoelectronics™ | TinyLogic®      |
| E <sup>2</sup> CMOS™                 | HiSeC™              | MSXPro™            | Quiet Series™       | TruTranslation™ |
| EnSigna™                             | I <sup>2</sup> C™   | OCX™               | RapidConfigure™     | UHC™            |
| Across the board. Around the world.™ |                     | OCXPro™            | RapidConnect™       | UltraFET®       |
| The Power Franchise™                 |                     | OPTOLOGIC®         | SILENT SWITCHER®    | VCX™            |
| Programmable Active Droop™           |                     | OPTOPLANAR™        | SMART START™        |                 |

## DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

## LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

## PRODUCT STATUS DEFINITIONS

### Definition of Terms

| Datasheet Identification | Product Status         | Definition                                                                                                                                                                                                            |
|--------------------------|------------------------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| Advance Information      | Formative or In Design | This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.                                                                                    |
| Preliminary              | First Production       | This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design. |
| No Identification Needed | Full Production        | This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.                                                       |
| Obsolete                 | Not In Production      | This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.                                                   |



**Стандарт  
Электрон  
Связь**

Мы молодая и активно развивающаяся компания в области поставок электронных компонентов. Мы поставляем электронные компоненты отечественного и импортного производства напрямую от производителей и с крупнейших складов мира.

Благодаря сотрудничеству с мировыми поставщиками мы осуществляем комплексные и плановые поставки широчайшего спектра электронных компонентов.

Собственная эффективная логистика и склад в обеспечивает надежную поставку продукции в точно указанные сроки по всей России.

Мы осуществляем техническую поддержку нашим клиентам и предпродажную проверку качества продукции. На все поставляемые продукты мы предоставляем гарантию .

Осуществляем поставки продукции под контролем ВП МО РФ на предприятия военно-промышленного комплекса России , а также работаем в рамках 275 ФЗ с открытием отдельных счетов в уполномоченном банке. Система менеджмента качества компании соответствует требованиям ГОСТ ISO 9001.

Минимальные сроки поставки, гибкие цены, неограниченный ассортимент и индивидуальный подход к клиентам являются основой для выстраивания долгосрочного и эффективного сотрудничества с предприятиями радиоэлектронной промышленности, предприятиями ВПК и научно-исследовательскими институтами России.

С нами вы становитесь еще успешнее!

**Наши контакты:**

**Телефон:** +7 812 627 14 35

**Электронная почта:** [sales@st-electron.ru](mailto:sales@st-electron.ru)

**Адрес:** 198099, Санкт-Петербург,  
Промышленная ул, дом № 19, литера Н,  
помещение 100-Н Офис 331